

AI 5. (*Amended*) A semiconductor active backplane according to claim 1 wherein the active element(s) have a MOS construction.

6. (*Amended*) A semiconductor active backplane according to claim 1 wherein substantially the whole of each active element is covered by a metallic conductor, or a pair of metallic conductors.

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AI 9. (*Amended*) A backplane according to claim 1 wherein the array of active elements is covered by an insulating layer, each said active element being connected to a metal electrode on said insulating layer, the array of said metal electrodes thus formed covering more than 65% of the area of said array.

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